

FIG. 1

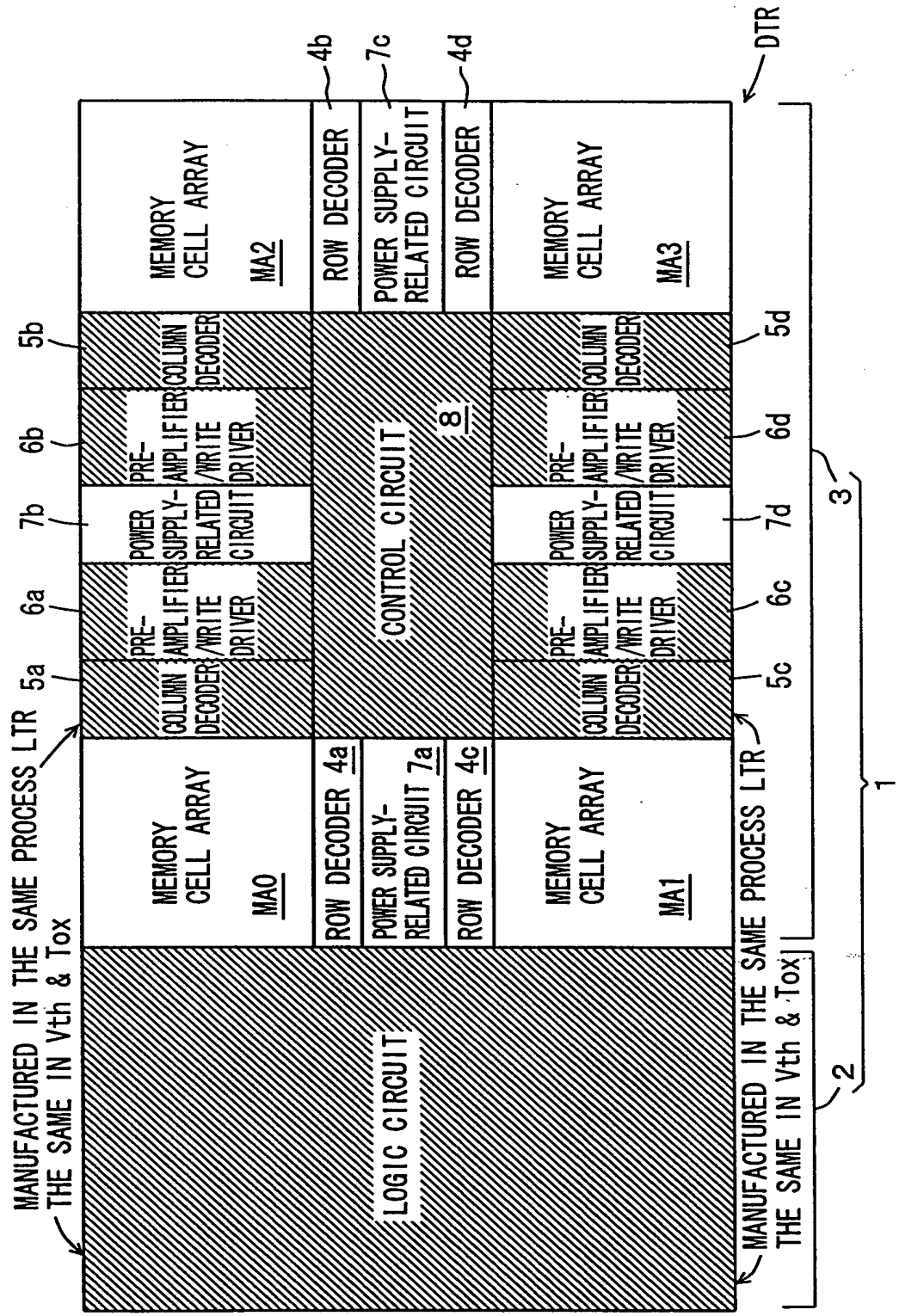


FIG. 2

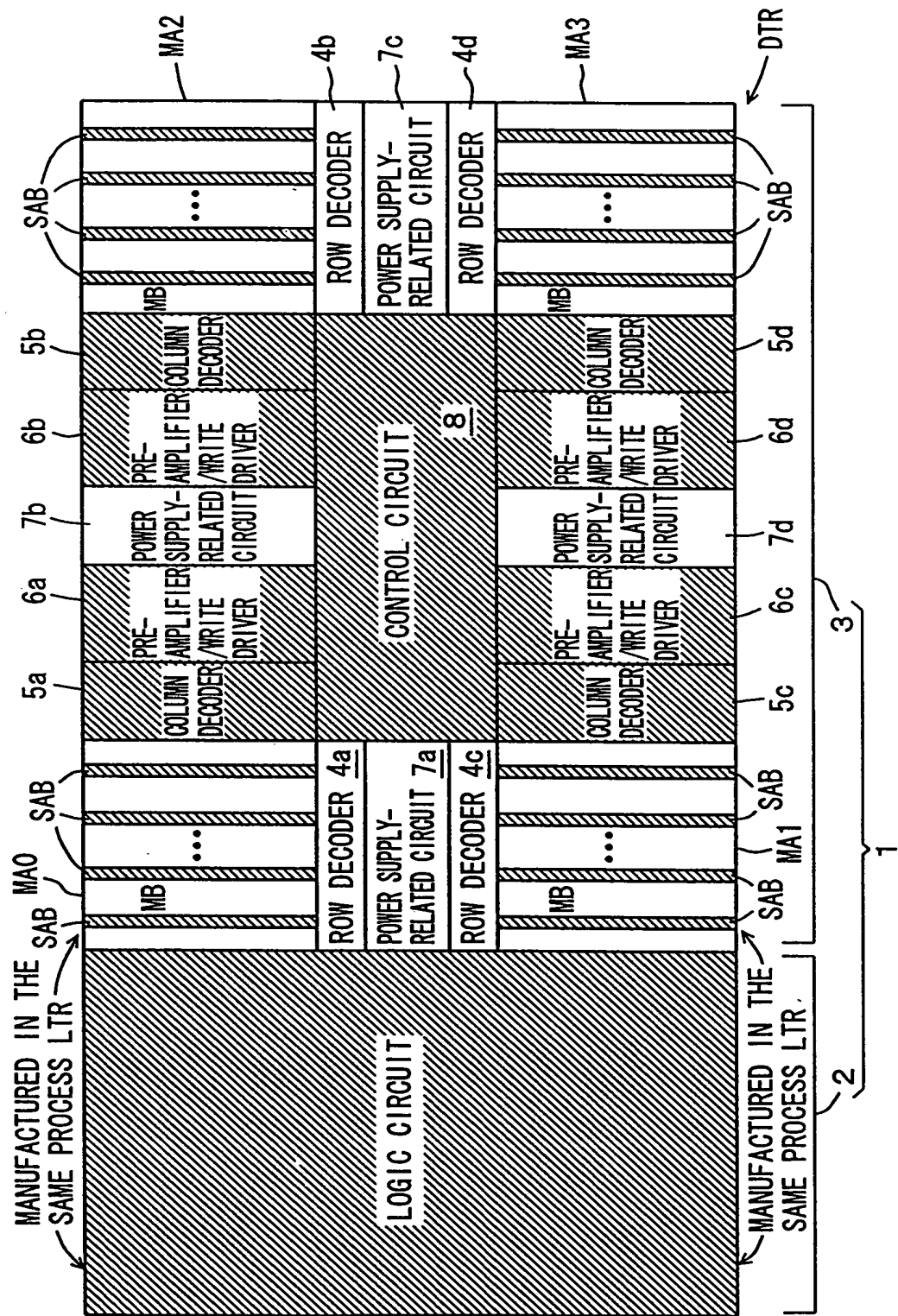


FIG. 3

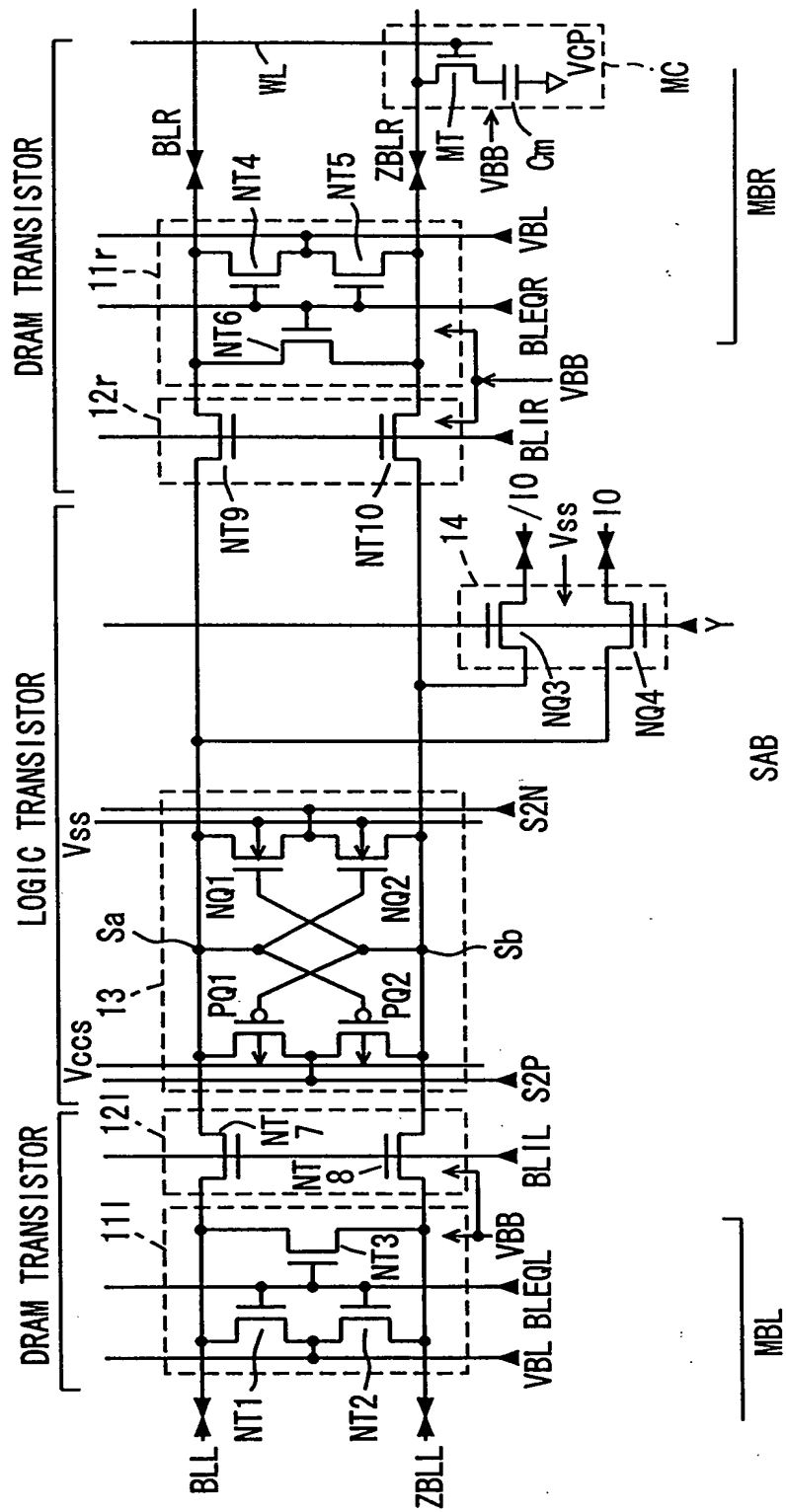


FIG. 4

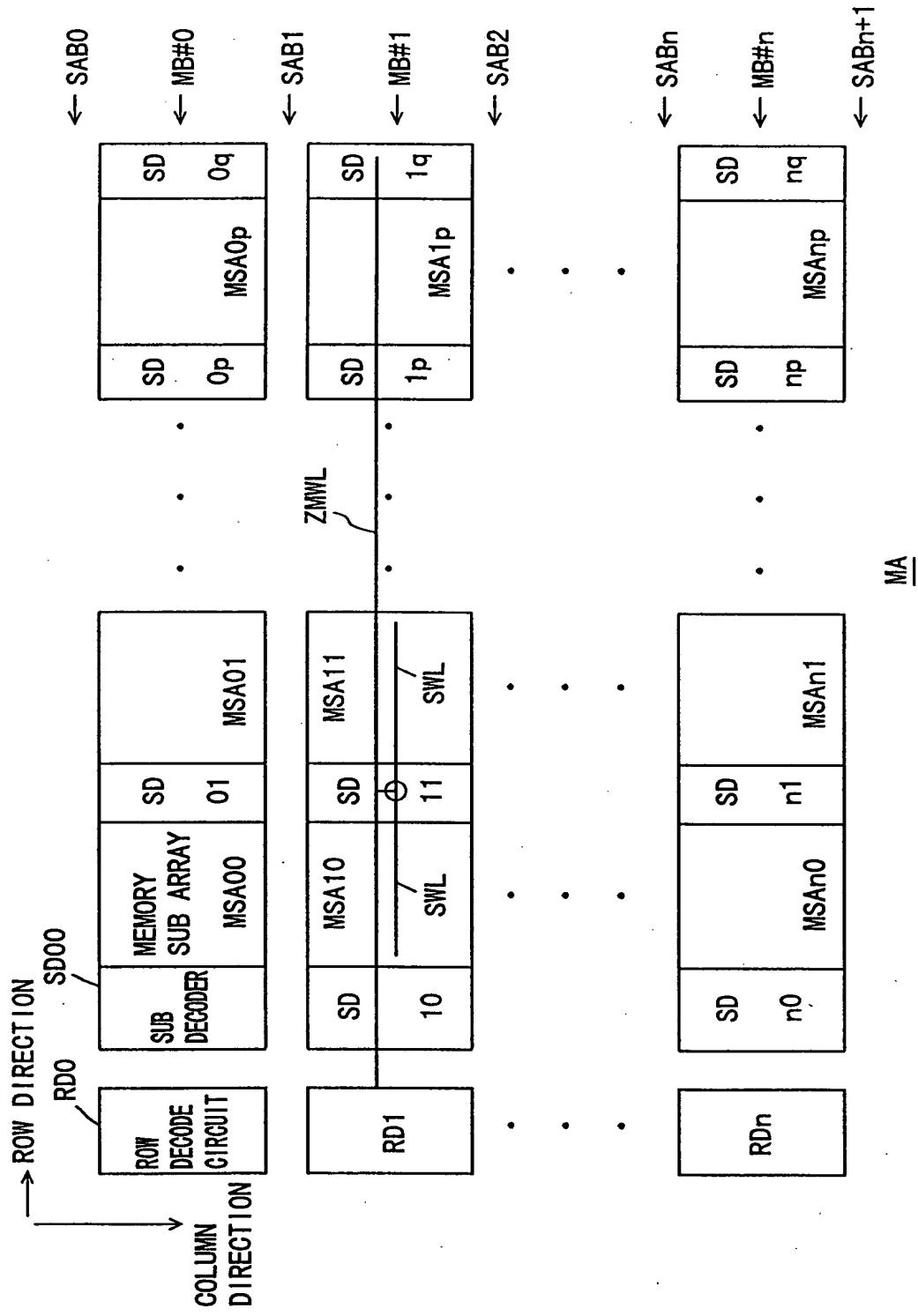


FIG. 5

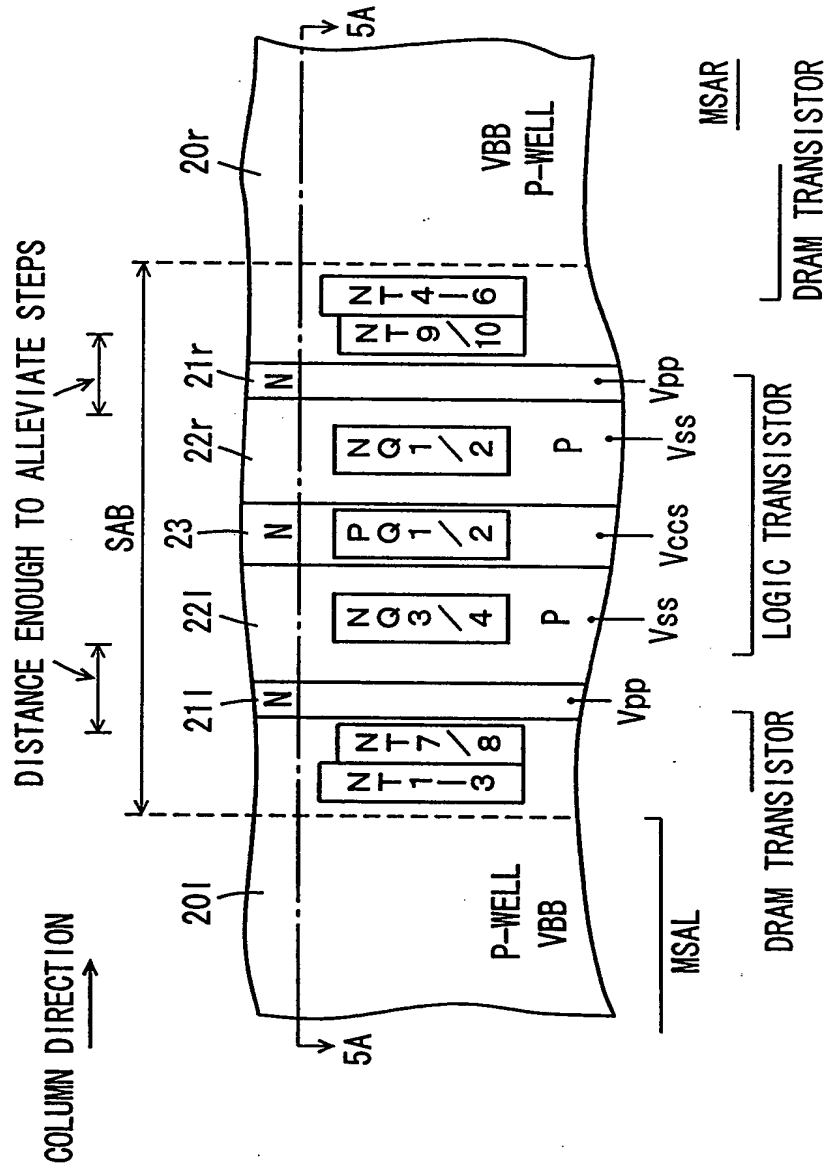


FIG. 6

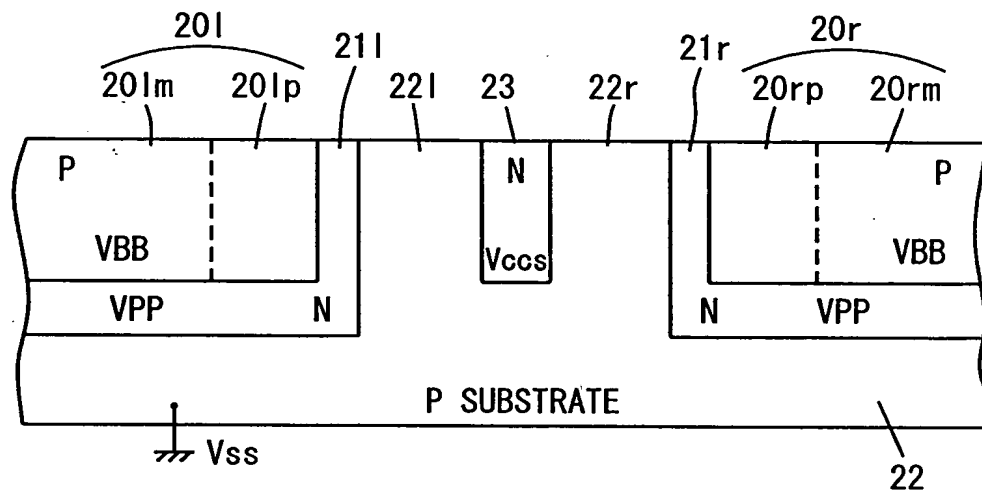


FIG. 7

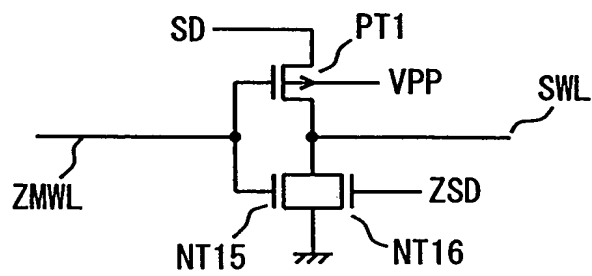


FIG. 8

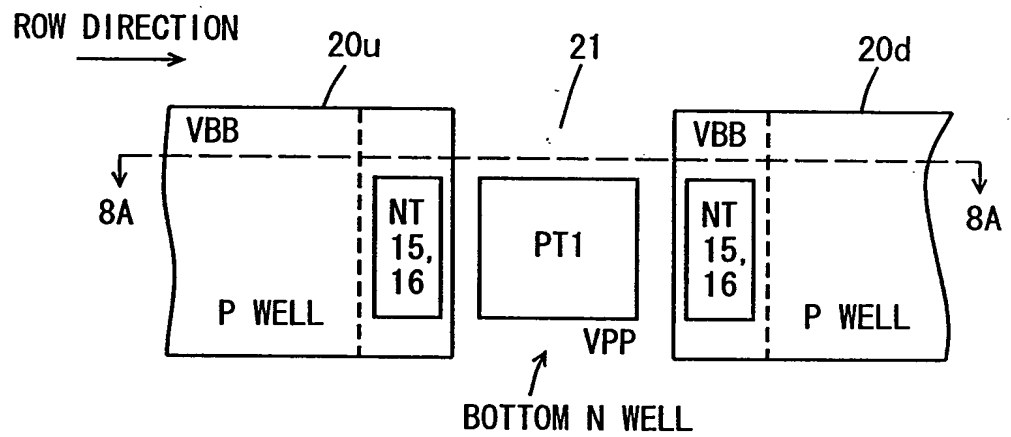


FIG. 9

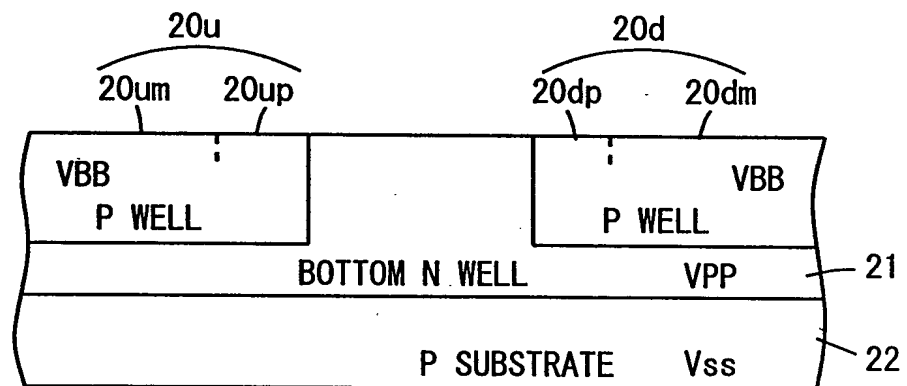


FIG. 10

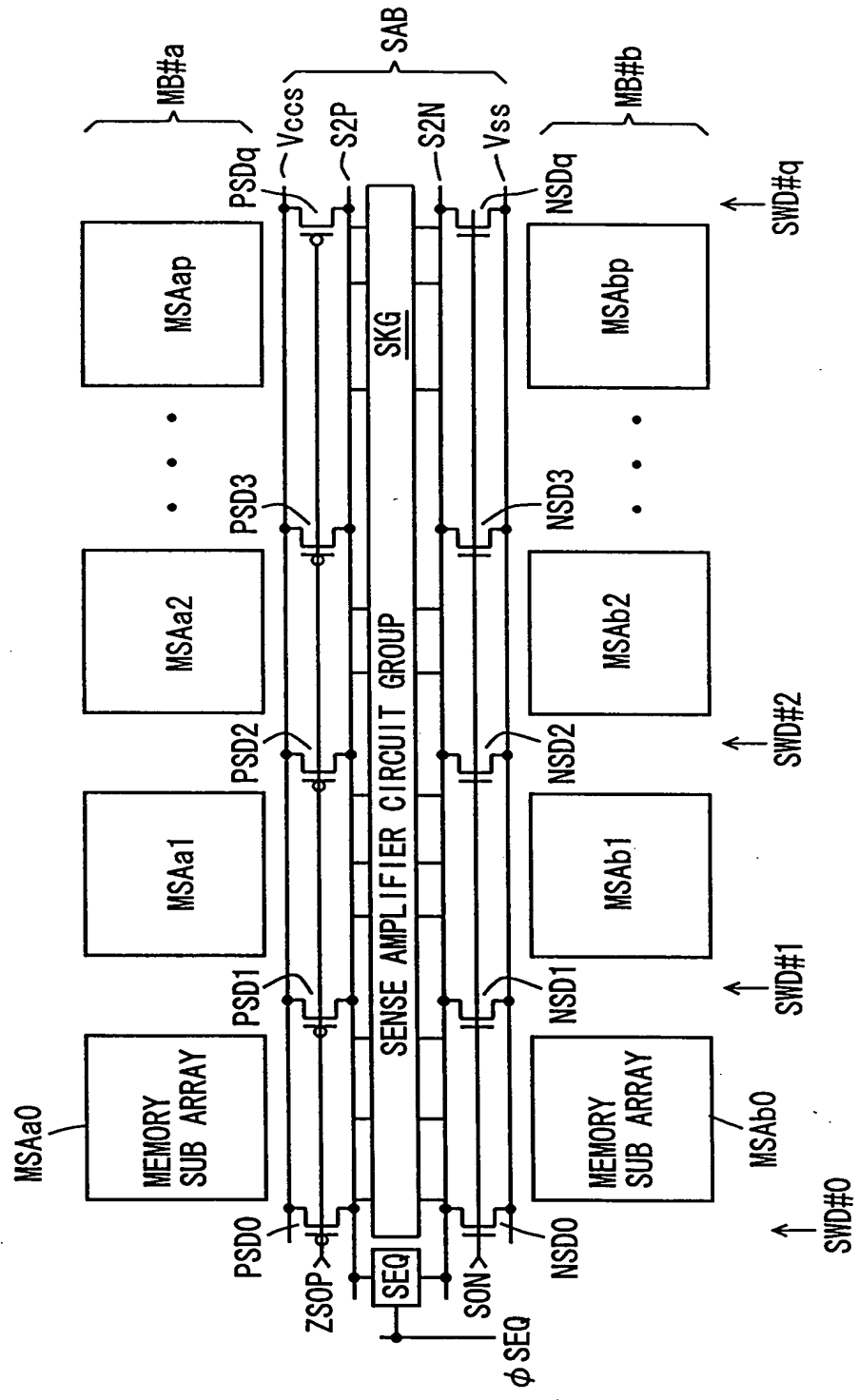




FIG. 11

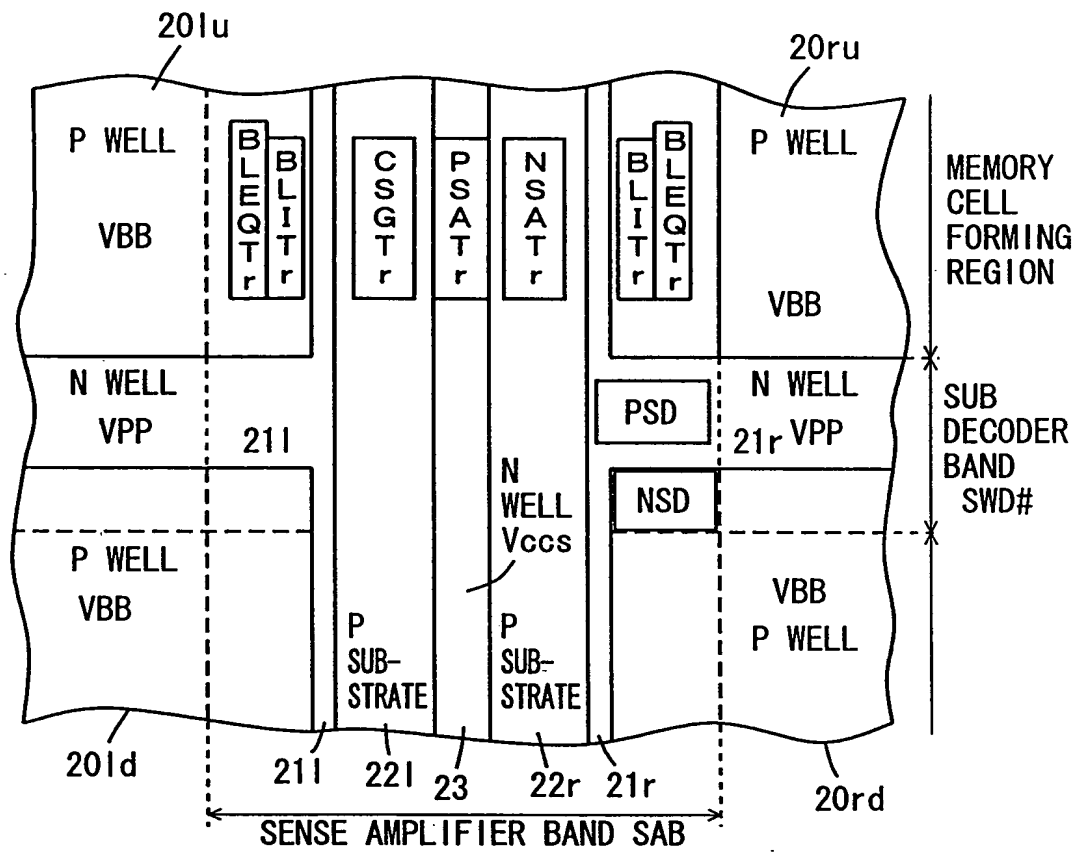
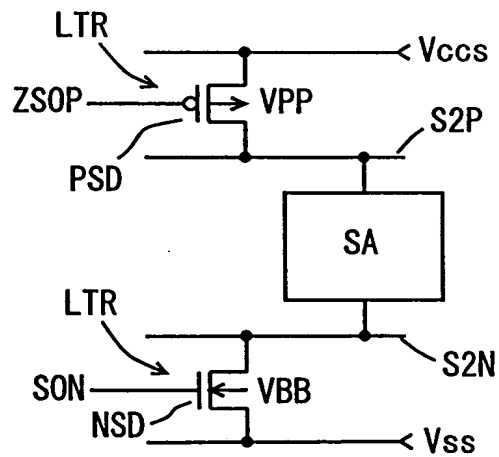


FIG. 12



The diagram illustrates a cross-sectional view of a semiconductor device, showing a sense amplifier band (SAB) and a memory cell forming region. The device is divided into three main sections: 20ld, 20ld, and 20rd. The central section is labeled 20lu and 20ru. The SAB is labeled 21l and 21r. The memory cell forming region is labeled 20ld and 20rd. The device is divided into three main sections: 20ld, 20ld, and 20rd. The central section is labeled 20lu and 20ru. The SAB is labeled 21l and 21r. The memory cell forming region is labeled 20ld and 20rd.

FIG. 15

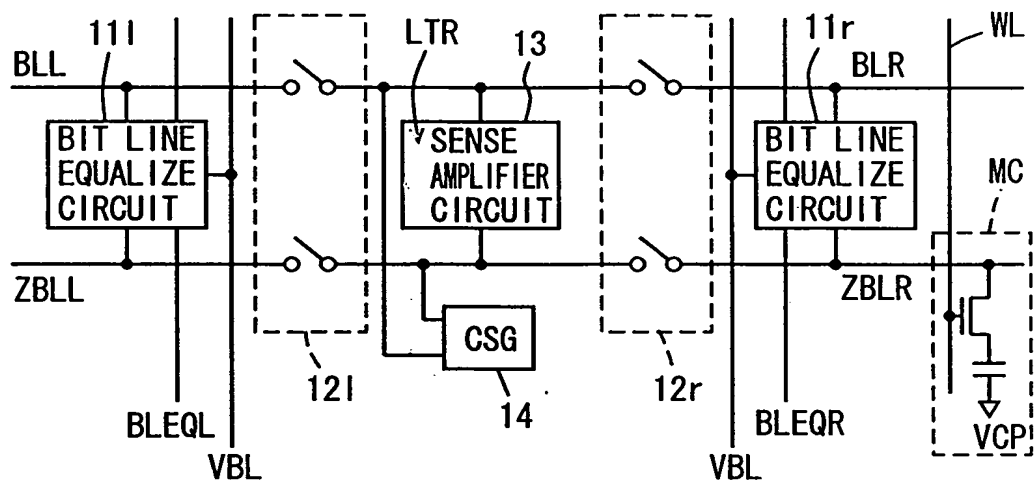


FIG. 16

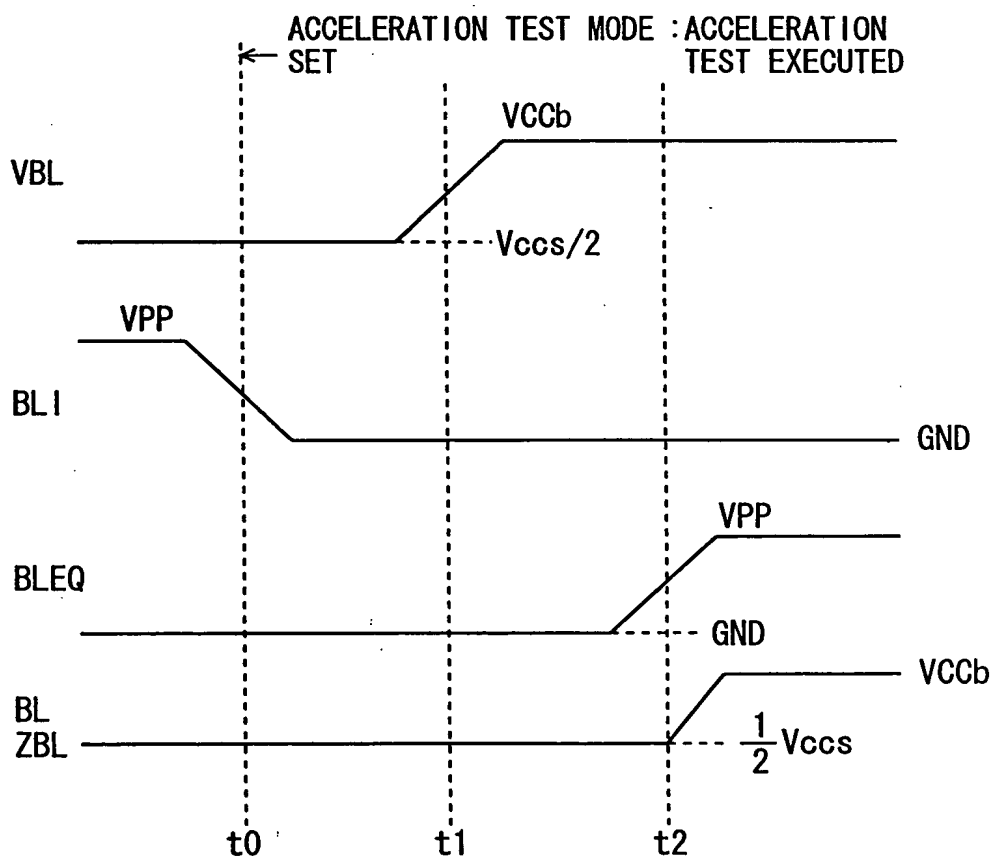


FIG. 17

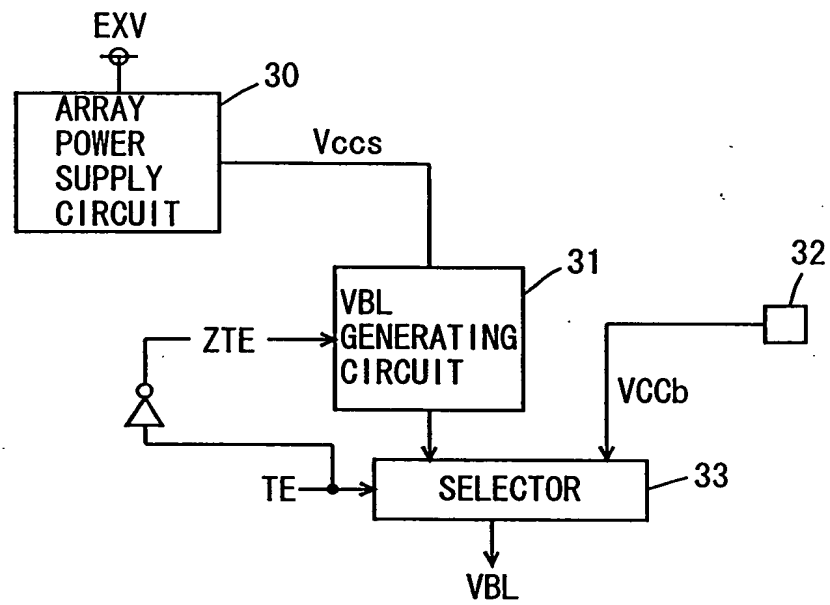


FIG. 18

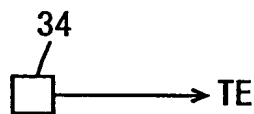


FIG. 19

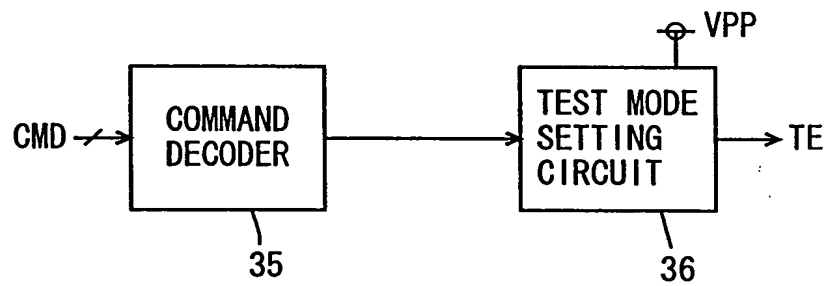


FIG. 20

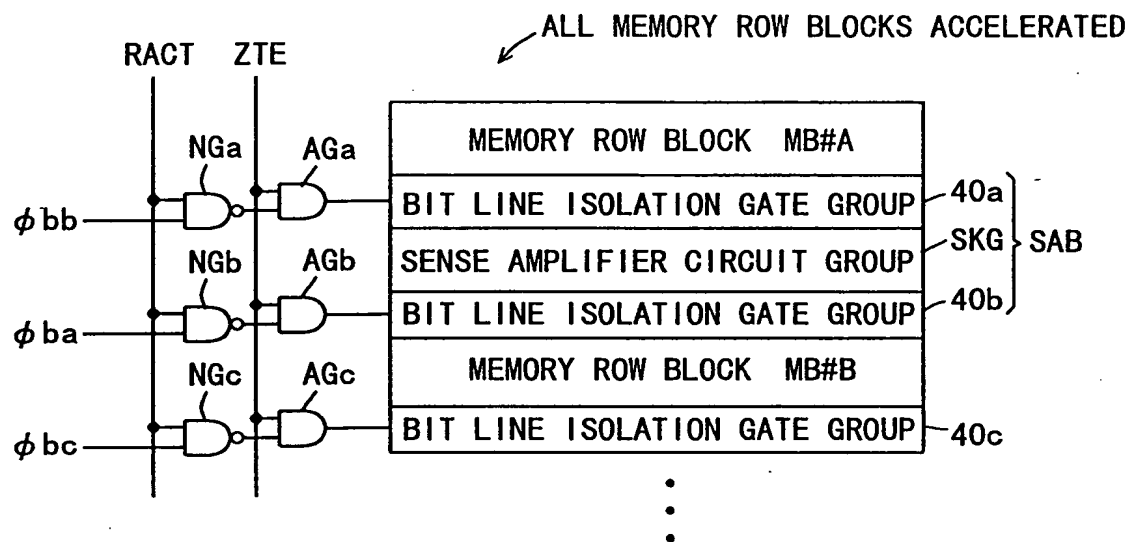


FIG. 21

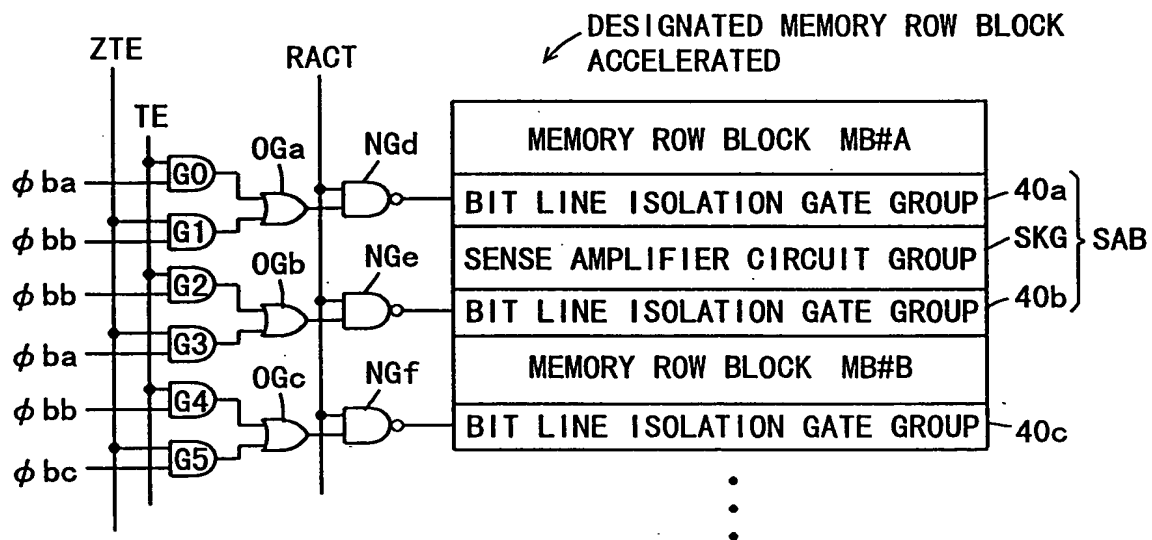


FIG. 22

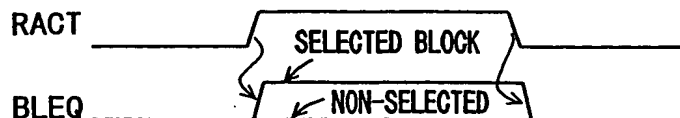


FIG. 23 A

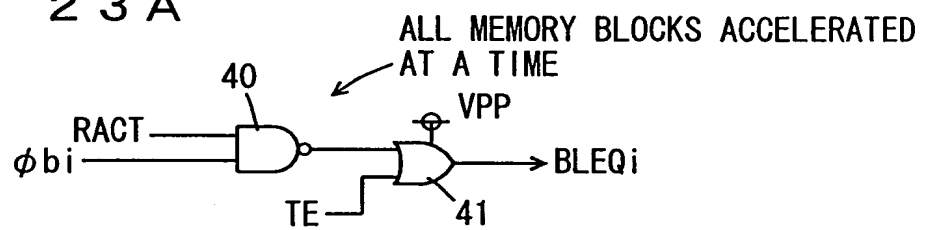


FIG. 23 B

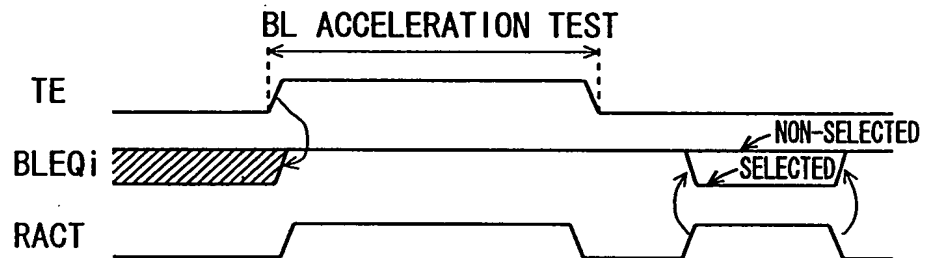


FIG. 24

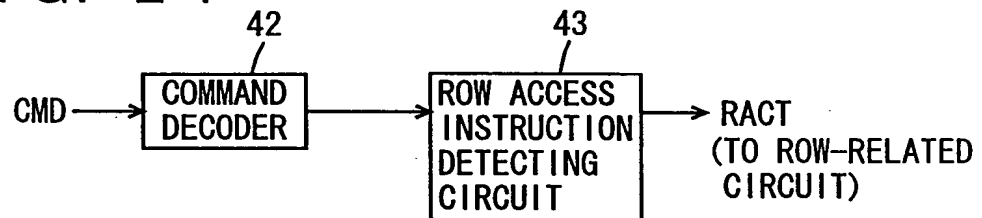


FIG. 25 A

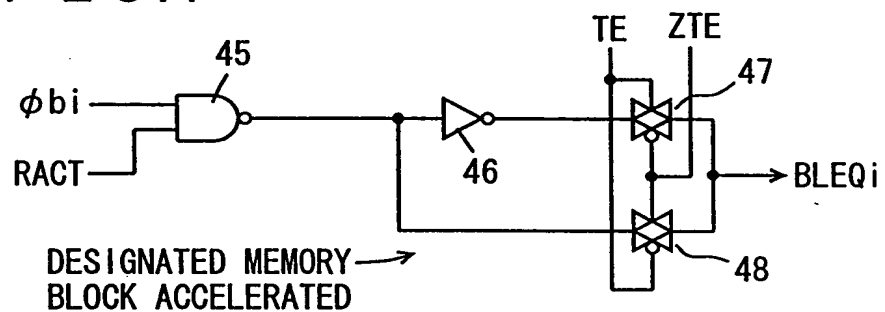


FIG. 25 B

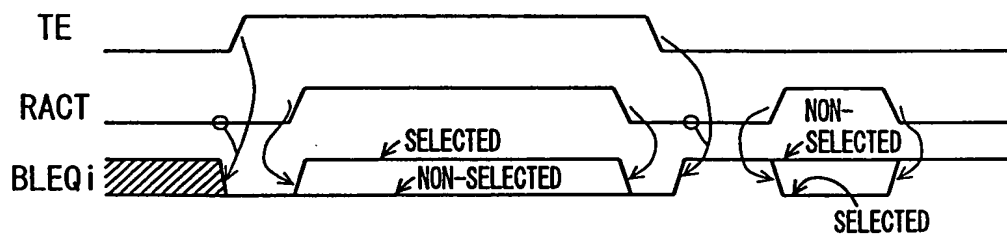


FIG. 26 PRIOR ART

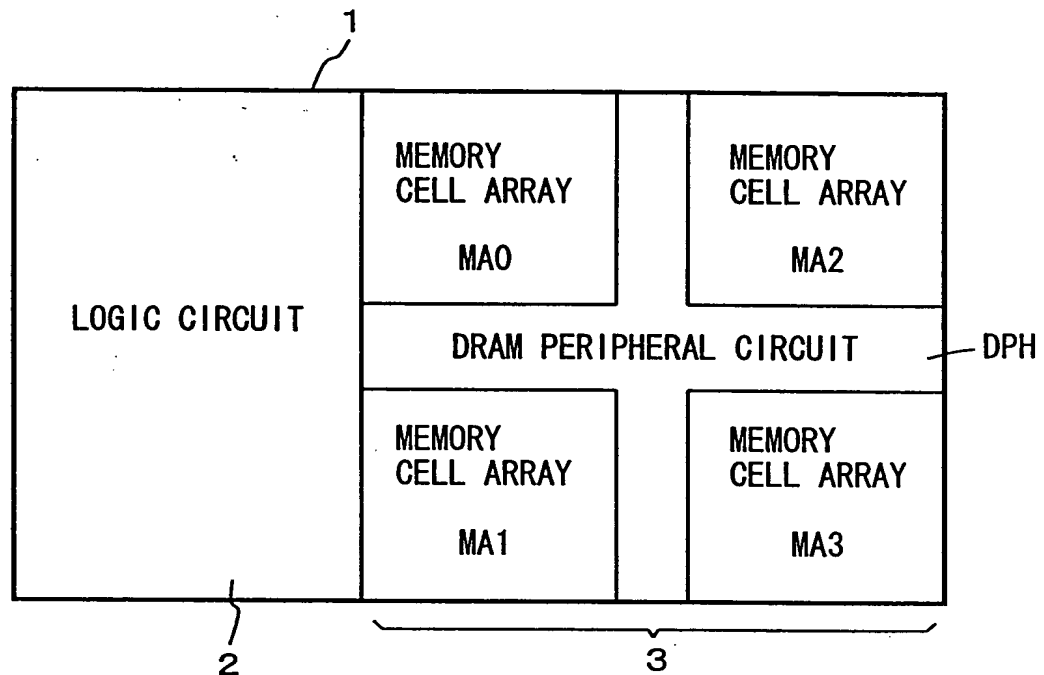
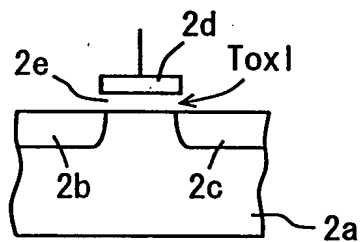
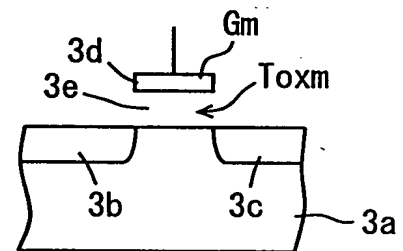


FIG. 27A  
PRIOR ART



LTR  
Low -  $V_{th}$

FIG. 27B  
PRIOR ART



DTR  
M -  $V_{th}$   
 $Toxm > Tox1$